Temperature Dependent Electronic Structure of A-site Ordered Perovskite CaCu₃Ti₄O₁₂

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1 Introduction

CaCu₃Ti₄O₁₂(CCTO) has A-site ordered perovskite structure (A'A₃B₄O₁₂). One of the four A-site (Cu) in the perovskite structure (ABO₃) is replaced by Ca-ion, so that the TiO₆ cluster in CCTO is tilted from crystallographic axis. CCTO exhibits a huge dielectric constant of $\varepsilon \sim 10^4$ in the temperature range of 100 to 600 K, while the dielectric constant decreases suddenly below about 100 K without a structural phase transition [1]. Since CCTO does not undergo structural phase transitions on the dielectric anomaly, it is important to study the electronic structure to understand the dielectric properties. In this study, resonant X-ray Raman scattering (XRS) [2-4] of CCTO was measured. Core excitations such as 2p3d and 2p4p, where underline denote a hole state, were observed. These spectra unoccupied density-of-states. reflect Temperature dependent XRS spectra were observed at Cu K absorption edge.

2 Experiment

Single crystal CCTO (100) was used in this experiment. The XRS spectra were measured using X-ray emission spectrometer (Escargot) at beamline BL-7C of Photon Factory. XRS measurements were carried out at temperatures of 15, 30, 80 and 120 K as well as room temperature. 80 and 120 K are below and just above the dielectric anomaly temperature, respectively. Helium circulation cryostat was used in these measurements.

3 Results and Discussion

Figure 1 shows the Cu K XAS spectrum of CCTO (100) measured by partial photon yield (PPY) method. Cu 3d states were observed at the pre-edge region, while the main structure shows Cu 4p state. The vertical bar denotes excitation energy in the XRS measurement.

Figure 2 shows the temperature dependent XRS spectra of CCTO (100) excited at 8980.2 eV. X-ray Emission spectra are plotted against energy loss (Raman shift). Four XRS peaks were observed with each core level of Cu $2p_{3/2}$ and $2p_{1/2}$. The P₁ and P₂ are originated from Cu $2p_{3d}$ excitations, while the P₃ and P₄ are originated from Cu 2p4p excitations. These spectra were normalized with P₃ peak intensity that reflects 4*p* state and does not change with excitation energy and temperature. The temperature dependence measurements show that the intensity of P₁ (P₁) decreases around 100K, then it increases again at low



Fig.1: Cu *K* XAS spectrum of CCTO (100). The vertical bars indicate the excitation energy of the XRS measurement.



Fig.2: Temperature dependence of the Cu *K* resonant Xray Raman scattering spectra of CCTO (100) excited at 8980.2 eV.

temperature. Since the XRS spectra reflect the unoccupied density of states, the result shows increase of Cu 3d state around dielectric anomaly temperature. Other hand, Ti 3d peak was observed decreasing continually with decreasing temperature in Ti K XRS measurements. These results suggest the relation between electronic state and dielectric properties.

References

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